

PNP General Purpose Amplifier

This device is designed for general purpose amplifier and switching applications at collector currents of 10 μ A to 100 mA.

Absolute Maximum Ratings* $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	40	V	
V _{CBO}	Collector-Base Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
Ic	Collector Current - Continuous	200	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

Symbol	Characteristic	Мах		Units	
		2N3906	*MMBT3906	**PZT3906	
P _D	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

T_A = 25°C unless otherwise noted

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

PNP General Purpose Amplifier (c

0.85

0.95

0.65

V

V

continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAF	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	5.0		V
BL	Base Cutoff Current	$V_{CE} = 30 \text{ V}, \text{ V}_{BE} = 3.0 \text{ V}$		50	nA
CEX	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, \text{ V}_{BE} = 3.0 \text{ V}$		50	nA
	ACTERISTICS			I	
n _{FE}	DC Current Gain *	$I_{C} = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	60 80		
		$I_{c} = 10 \text{ mA}, V_{cE} = 1.0 \text{ V}$	100	300	
		$I_{\rm C} = 50 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	60		
		$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	30		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$		0.25 0.4	V V

 $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$

 $I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$

SMALL SIGNAL CHARACTERISTICS

Base-Emitter Saturation Voltage

V_{BE(sat)}

f _T	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	250		MHz
C _{obo}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ f = 100 kHz		4.5	pF
Cibo	Input Capacitance	$V_{EB} = 0.5 V, I_C = 0,$ f = 100 kHz		10.0	pF
NF	Noise Figure	I_{C} = 100 μA, V _{CE} = 5.0 V, R _S =1.0kΩ,f=10 Hz to 15.7 kHz		4.0	dB

SWITCHING CHARACTERISTICS

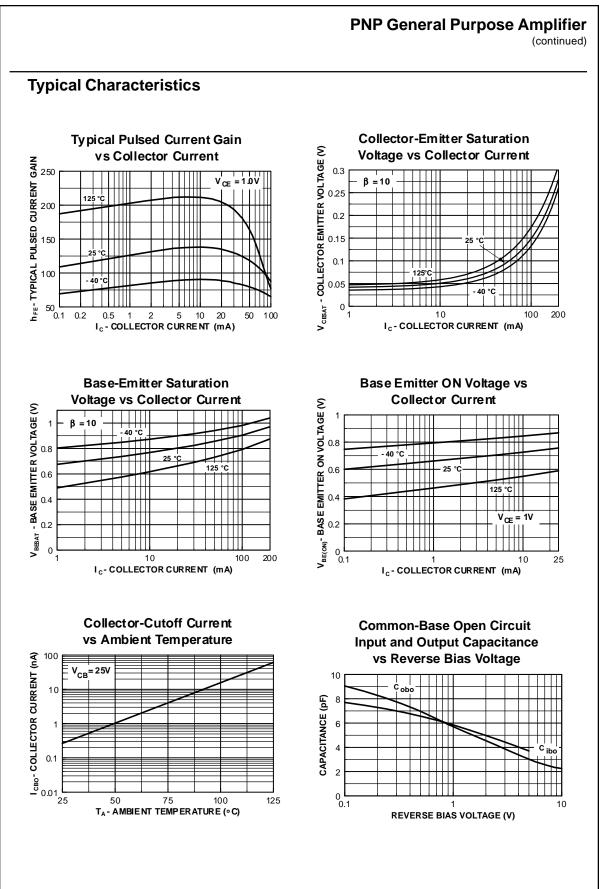
t _d	Delay Time	$V_{CC} = 3.0 \text{ V}, V_{BE} = 0.5 \text{ V},$	35	ns
t _r	Rise Time	$I_{\rm C} = 10$ mA, $I_{\rm B1} = 1.0$ mA	35	ns
ts	Storage Time	$V_{CC} = 3.0 \text{ V}, I_{C} = 10 \text{mA}$	225	ns
t _f	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$	75	ns

*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

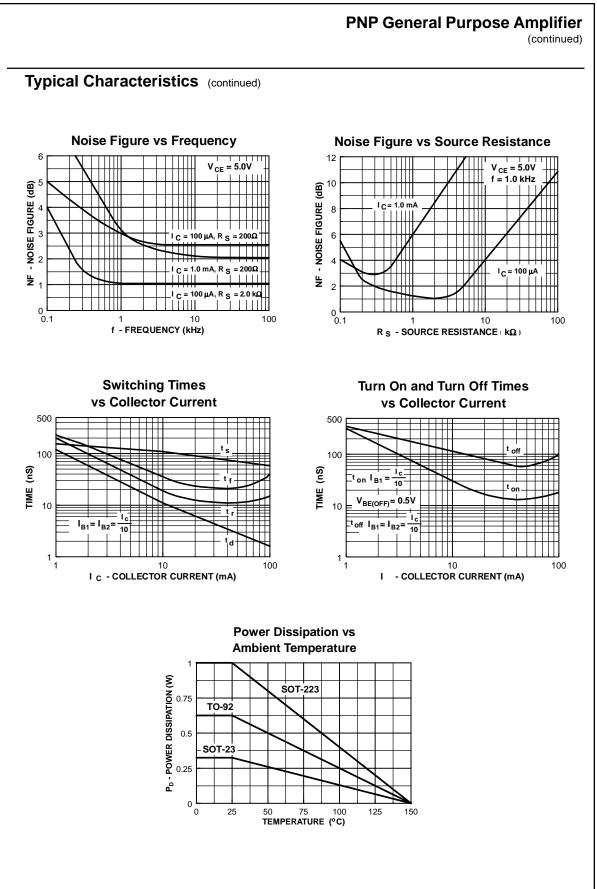
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

Spice Model

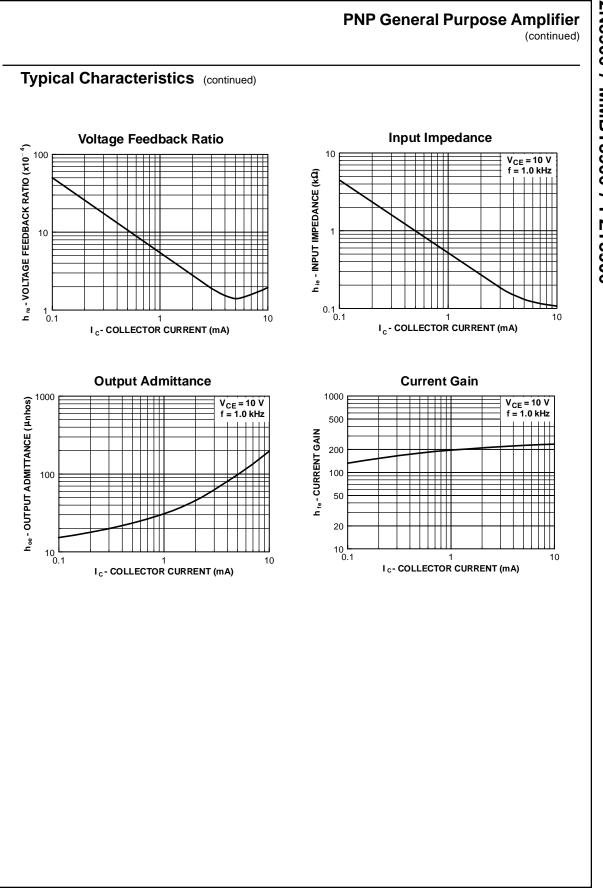
PNP (Is=1.41f Xti=3 Eg=1.11 Vaf=18.7 Bf=180.7 Ne=1.5 Ise=0 Ikf=80m Xtb=1.5 Br=4.977 Nc=2 Isc=0 Ikr=0 Rc=2.5 Cjc=9.728p Mjc=.5776 Vjc=.75 Fc=.5 Cje=8.063p Mje=.3677 Vje=.75 Tr=33.42n Tf=179.3p Itf=.4 Vtf=4 Xtf=6 Rb=10)



2N3906 / MMBT3906 / PZT3906



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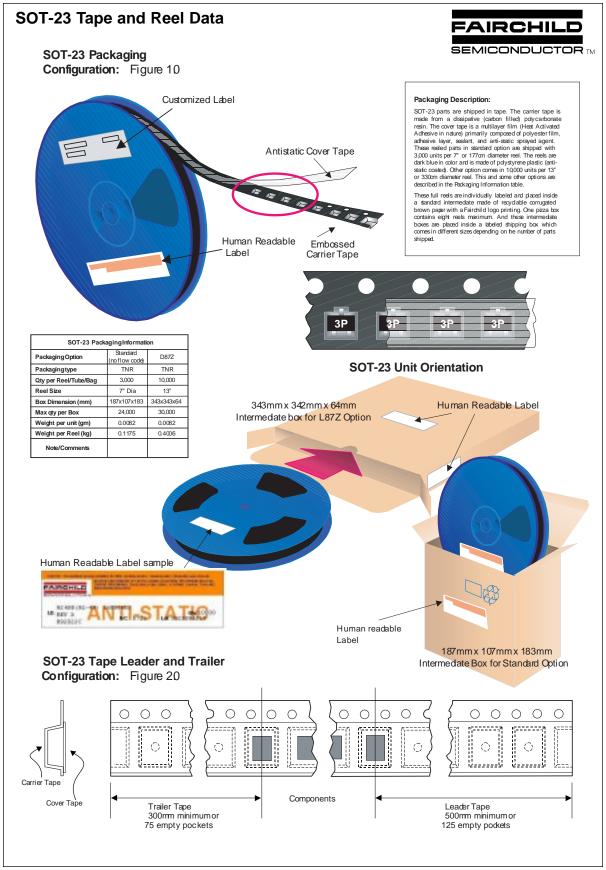
March 2001, Rev. B1





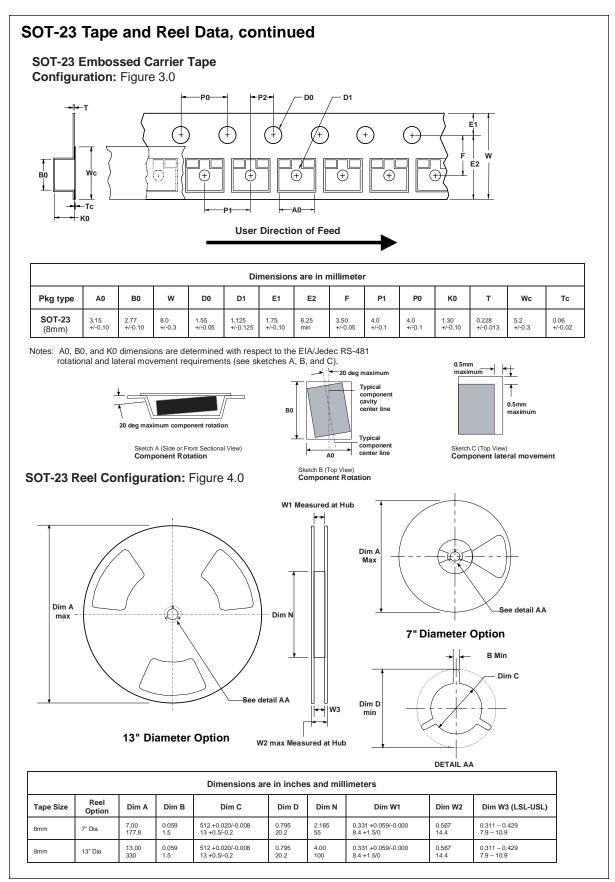
July 1999, Rev. A



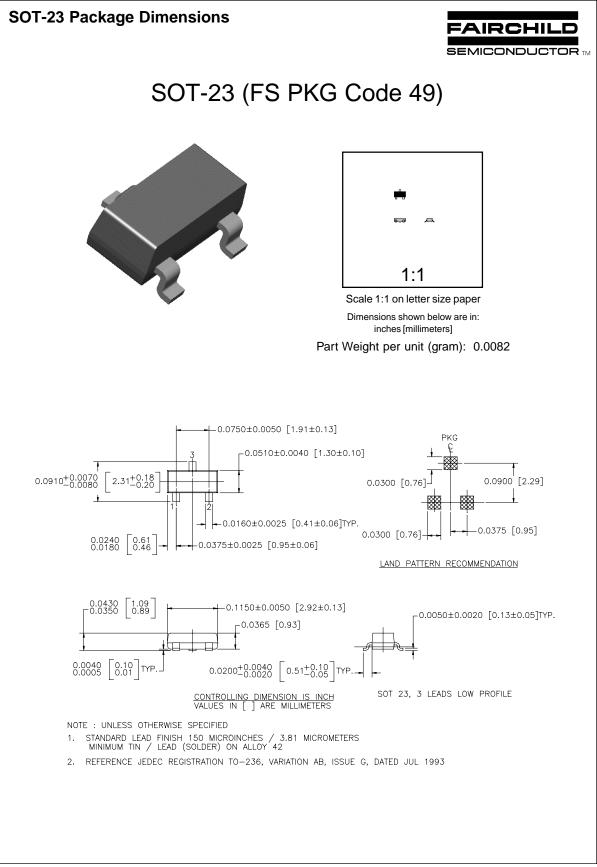


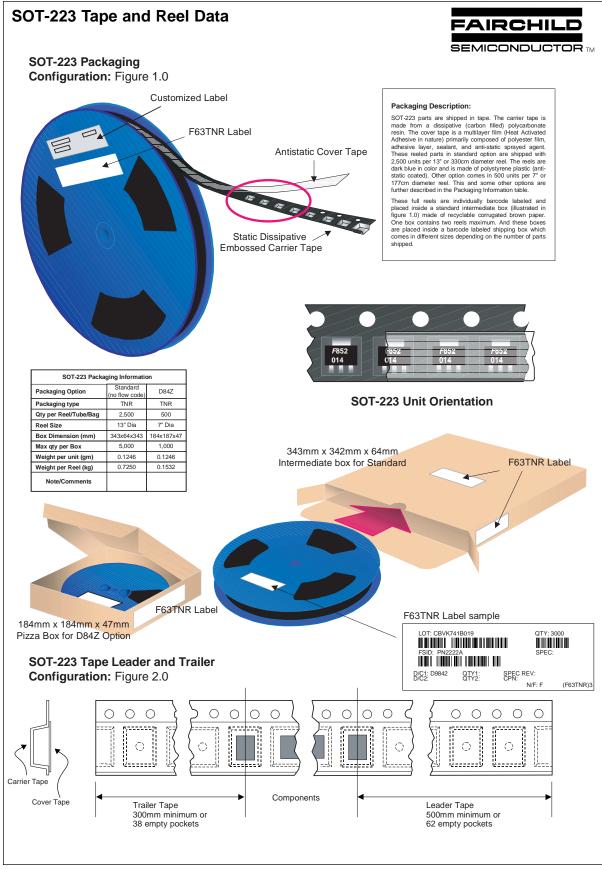
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September 1999, Rev. C



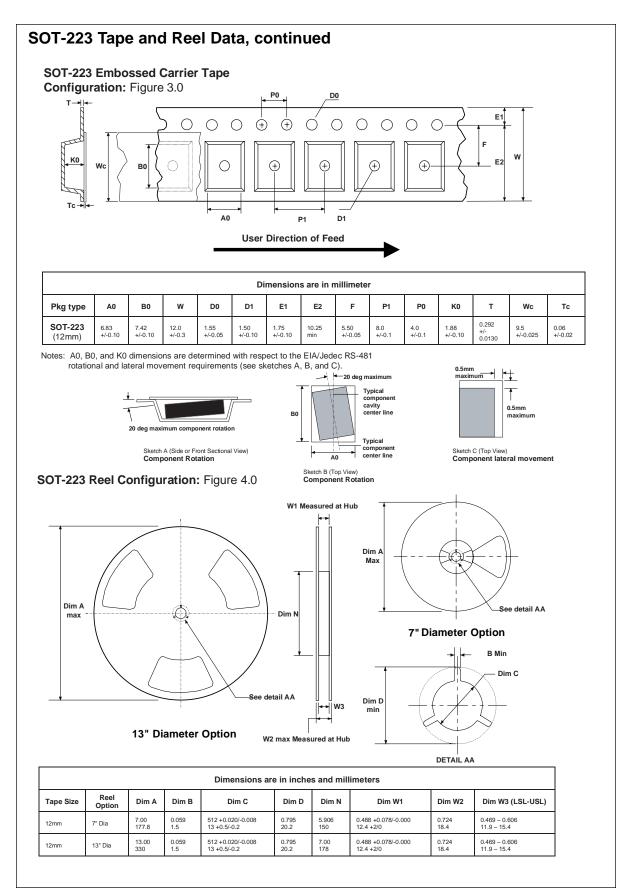
September 1999, Rev. C

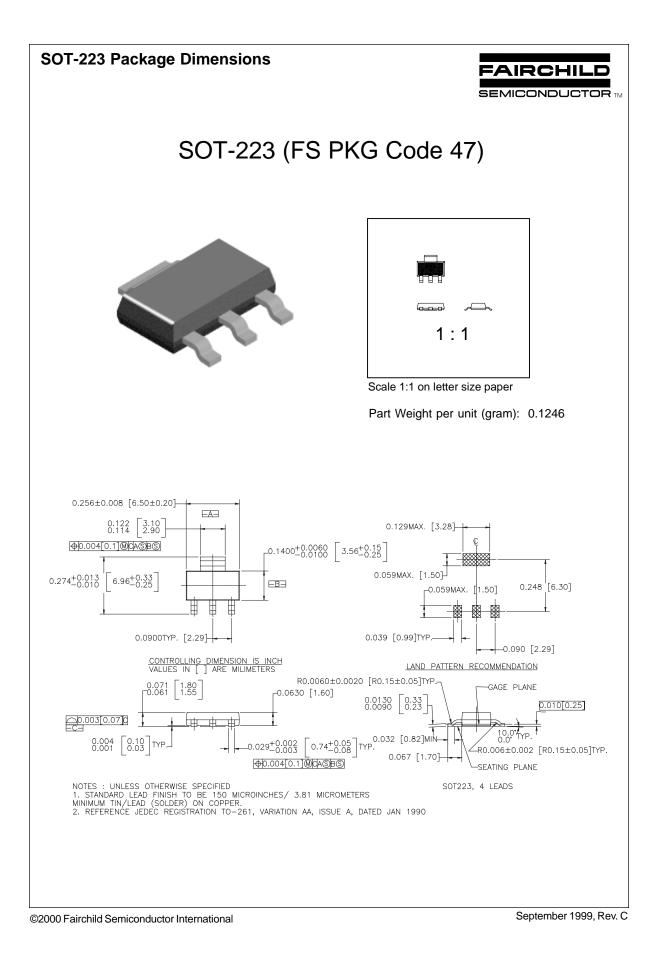




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